Silicon NPN Darlington Power Transistors 2SD2494

DESCRIPTION

·With TO-3PML package

·Complement to type 2SB1625

APPLICATIONS

·Audio,series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

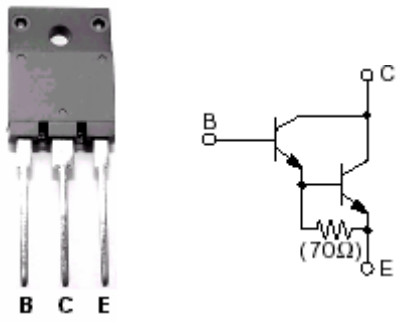

Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	110	V
V_{CEO}	Collector-emitter voltage	Open base	110	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
I_B	Base current		1	A
P_C	Collector power dissipation	T_C=25□	60	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA; I_B=0	110			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5 A;I_B=5m A			2.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5 A;I_B=5m A			3.0	V
I_{CBO}	Collector cut-off current	V_{CB}=110V; I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=4V	5000			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=12V		60		MHz
C_{OB}	Output capacitance	I_E=0; V_{CB}=10V;f=1MHz		55		pF
Switching times						
t_{on}	Turn-on time	I_C=5A;R_L=6Ω I_{B1}=-I_{B2}=5mA V_{CC}=30V		0.8		μs
t_s	Storage time			6.2		μs
t_f	Fall time			1.1		μs

◆ **h_{FE} classifications**

O	P	Y
5000-12000	6500-20000	15000-30000

PACKAGE OUTLINE

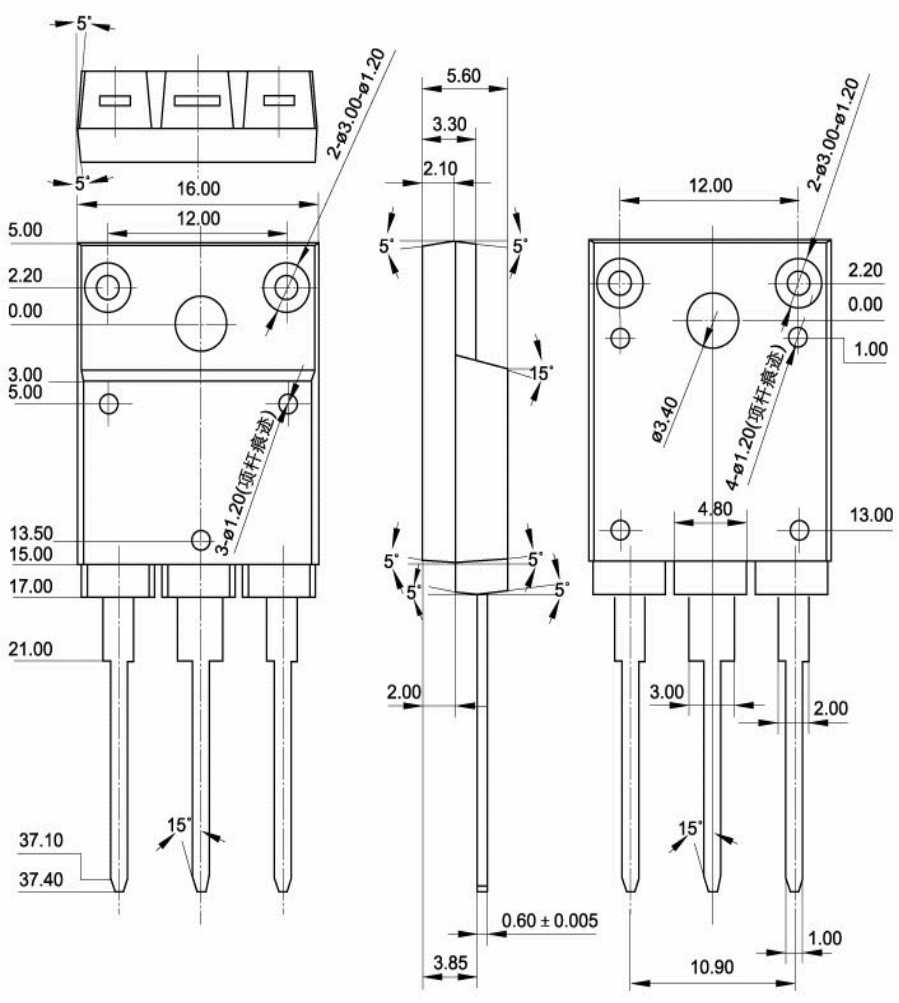

Fig.2 Outline dimensions